

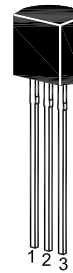
# ST 2SC1674

## NPN Silicon Epitaxial Planar Transistor

TV PIF amplifier, FM tuner RF amplifier.

The transistor is subdivided into three groups, R, O, and Y, according to its DC current gain

On special request, these transistors can be manufactured in different pin configurations.



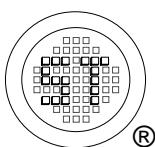
1. Emitter 2. Collector 3. Base  
TO-92 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	30	V
Collector Emitter Voltage	$V_{CEO}$	20	V
Emitter Base Voltage	$V_{EBO}$	4	V
Collector Current	$I_C$	20	mA
Power Dissipation	$P_{tot}$	250	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE} = 6\text{ V}$ , $I_C = 1\text{ mA}$	Current Gain Group R O Y	$h_{FE}$	40	-	80	-
		$h_{FE}$	70	-	140	-
		$h_{FE}$	120	-	240	-
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	$I_{CBO}$	-	-	100	nA	
Emitter Base Cutoff Current at $V_{EB} = 4\text{ V}$	$I_{EBO}$	-	-	100	nA	
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	30	-	-	V	
Collector Emitter Breakdown Voltage at $I_C = 5\text{ mA}$	$V_{(BR)CEO}$	20	-	-	V	
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	4	-	-	V	
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$ , $I_B = 1\text{ mA}$	$V_{CE(sat)}$	-	-	0.3	V	
Gain Bandwidth Product at $V_{CE} = 6\text{ V}$ , $I_C = 1\text{ mA}$	$f_T$	-	600	-	MHz	
Output Capacitance at $V_{CB} = 6\text{ V}$ , $f = 1\text{ MHz}$	$C_{ob}$	-	1.2	-	pF	



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